





## **General Descriptions**

 DDC144NS features discrete dual NPN transistors that can support continuous maximum current up to 100 mA. It is suited for applications where the load needs to be turned on and off using circuits like micro-controllers, comparators, etc., particularly at a point of load. The component devices can be used as a part of a circuit or as a stand alone discrete device.

### **Features**

- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

### **Mechanical Data**

- Case: SOT-363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Figure 2
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.0065 grams (approximate)



Fig. 1: SOT-363

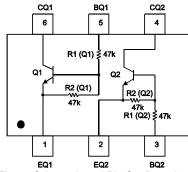


Fig. 2: Schematic and Pin Configuration

# Maximum Ratings, Total Device @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 3)	P <sub>d</sub>	200	mW
Thermal Resistance, Junction to Ambient Air	(Note 3)	$R_{ heta JA}$	625	°C/W
Operating and Storage Temperature Range		T <sub>i</sub> , T <sub>STG</sub>	-55 to +150	°C
Collector Current		I <sub>C</sub> (max)	100	mA

# **Maximum Ratings:**

# Sub-Component Device - Pre-Biased NPN Transistor @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V <sub>cc</sub>	50	V
Input Voltage	V <sub>in</sub>	-10 to +40	V
Output Current	lo	100	mA

# **Electrical Characteristics:**

### **Pre-Biased NPN Transistor** @T<sub>A</sub> = 25°C unless otherwise specified

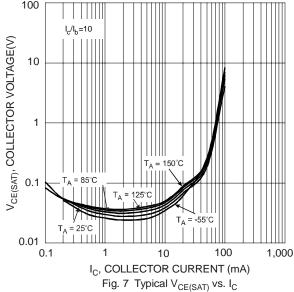
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	$V_{I(off)}$	0.5	1.1	_	V	$V_{cc} = 5V, I_{O} = 100uA$
input voltage	$V_{I(on)}$	_	1.5	3	V	$V_O = 0.3V, I_O = 2mA$
Output Voltage	$V_{O(on)}$	_	0.1	0.3	V	$I_{O}/I_{I} = 10 \text{mA}/0.5 \text{mA}$
Input Current	I <sub>I</sub>	_	_	0.18	mA	$V_I = 5V$
Output Current	I <sub>O(off)</sub>	_	_	0.5	uA	$V_{cc} = 50V, V_{I} = 0V$
DC Current Gain	Gl	100	_	_	_	$V_{O} = 5V, I_{O} = 5mA$
Input Resistor (R1) Tolerance	Δ R1	-30	_	+30	%	_
Resistance Ratio Tolerance	R2/R1	-20	_	+20	%	_
Gain-Bandwidth Product	f⊤	_	250	_	MHz	$V_{CF} = 10V$ , $I_F = 5mA$ , $f = 100 MH$

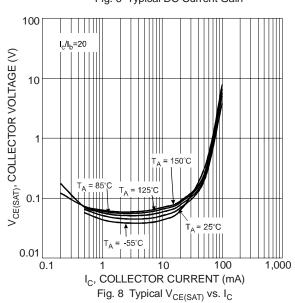
Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on page 4 or go to Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf

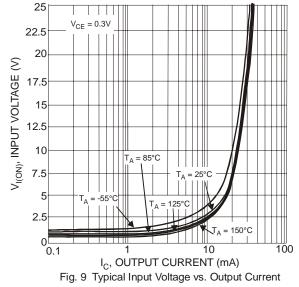


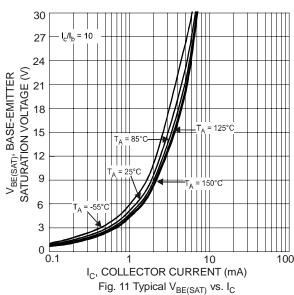
#### Typical Characteristics of NPN Transistor @ T<sub>A</sub> = 25°C unless otherwise specified 250 0.08 0.07 P<sub>D</sub>, POWER DISSIPATION (mW) 200 I<sub>C</sub>, COLLECTOR CURRENT (A) 0.06 $I_b = 0.3 \text{mA}$ 0.05 I<sub>b</sub> = 0.25mA 150 0.04 100 0.03 $I_b = 0.1 mA$ 0.02 = 0.15mA 50 R<sub>0JA</sub> = 625 °C/W 0.01 0 -50 0 50 100 150 0.2 0.4 0.6 0.8 1 1.2 1.4 1.6 1.8 T<sub>A</sub>, AMBIENT TEMPERATURE (°C) $V_{CE}$ , COLLECTOR EMITTER VOLTAGE (V) Fig. 3 Derating Curve Fig. 4 Typical $V_{CE}$ vs. $I_{C}$ 450 T<sub>A</sub> = 150°C T<sub>A</sub> = 150°C V<sub>CE</sub> = 10V 400 400 DC CURRENT GAIN 350 350 h<sub>FE</sub>, DC CURRENT GAIN 300 300 250 250 200 200 h<sub>E</sub>, 150 150 100 100 50 50 0 0.1 10 100 1,000 10 100 1,000 ${\rm I}_{\rm C}$ COLLECTOR CURRENT (mA) $I_C$ , COLLECTOR CURRENT (mA) Fig. 5 Typical DC Current Gain Fig. 6 Typical DC Current Gain 100 100 $I_{c}/I_{b}=20$ $I_c/I_b=10$ 10 10

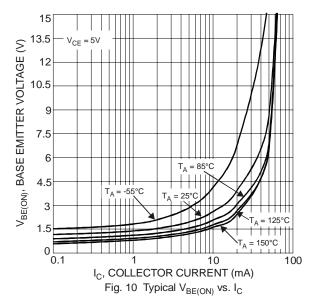


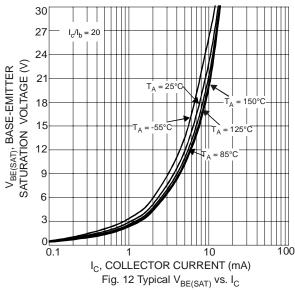










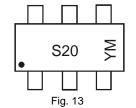


### Ordering Information (Note 4)

Device	Packaging	Shipping
DDC144NS-7	SOT-363	3000/Tape & Reel

Notes: 4. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**



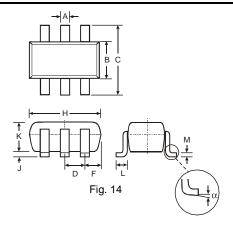
S20 = Product Type Marking Code, YM = Date Code Marking Y = Year, e.g., T = 2006 M = Month, e.g., 9 = September

Date Code Key

Year	2005	;	2006	2007		2008	2009		2010	2011		2012
Code	S		T	U		V	W		Χ	Y		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

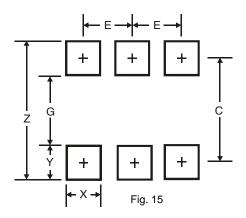


## **Package Outline Dimensions**



SOT-363					
Dim	Min	Max			
Α	0.10	0.30			
В	1.15	1.35			
C	2.00	2.20			
D	0.65 Nominal				
F	0.30 0.40				
Н	1.80	2.20			
7	_	0.10			
K	0.90 1.00				
٦	0.25	0.40			
М	0.10	0.25			
α	0°	8°			
All Dimensions in mm					

# Suggested Pad Layout



Dimensions	SOT-363*
Z	2.5
G	1.3
Х	0.42
Y	0.6
С	1.9
E	0.65

<sup>\*</sup> Typical dimensions in mm

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